

**100V, 137A, 4.5 mΩ N-channel Power SGT MOSFET**
**JMSL1004TG**
**Features**

- Excellent  $R_{DS(ON)}$  and Low Gate Charge
- 100% UIS Tested
- 100%  $\Delta V_{ds}$  Tested
- Halogen-free; RoHS-compliant

**Applications**

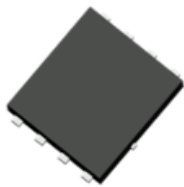
- Load Switch
- PWM Application
- Power Management

**Product Summary**

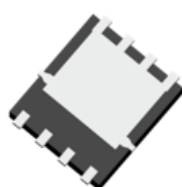
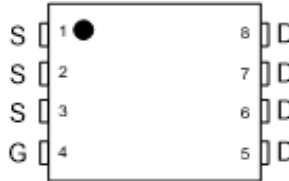
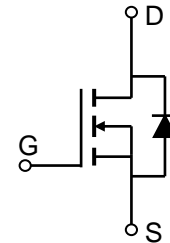
Parameters	Value	Unit
$V_{DSS}$	100	V
$V_{GS(th\_Typ)}$	1.7	V
$I_D(@V_{GS}=10V)$	137	A
$R_{DS(ON\_Typ)}(@V_{GS}=10V)$	3.3	mΩ
$R_{DS(ON\_Typ)}(@V_{GS}=4.5V)$	4.5	mΩ



Top View



Bottom View


**PDFN5X6-8L**

**Pin Assignment**

**Schematic Diagram**
**Ordering Information**

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMSL1004TG-13	SL1004T	1	Tape&Reel	PDFN5x6-8L	5000	50000

**Absolute Maximum Ratings** (@  $T_C = 25^\circ\text{C}$  unless otherwise specified)

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-to-Source Voltage	100	V
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$I_D$	Continuous Drain Current	$T_C = 25^\circ\text{C}$	137
		$T_C = 100^\circ\text{C}$	87
$I_{DM}$	Pulsed Drain Current <sup>(1)</sup>	Refer to Fig.4	A
$E_{AS}$	Single Pulsed Avalanche Energy <sup>(2)</sup>	497	mJ
$P_D$	Power Dissipation	$T_C = 25^\circ\text{C}$	141
		$T_C = 100^\circ\text{C}$	57
$T_J, T_{STG}$	Junction & Storage Temperature Range	-55 to 150	$^\circ\text{C}$

**Thermal Characteristics**

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient <sup>(3)</sup>	44	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.9	

**Electrical Characteristics** ( $T_J = 25^\circ\text{C}$  unless otherwise specified)

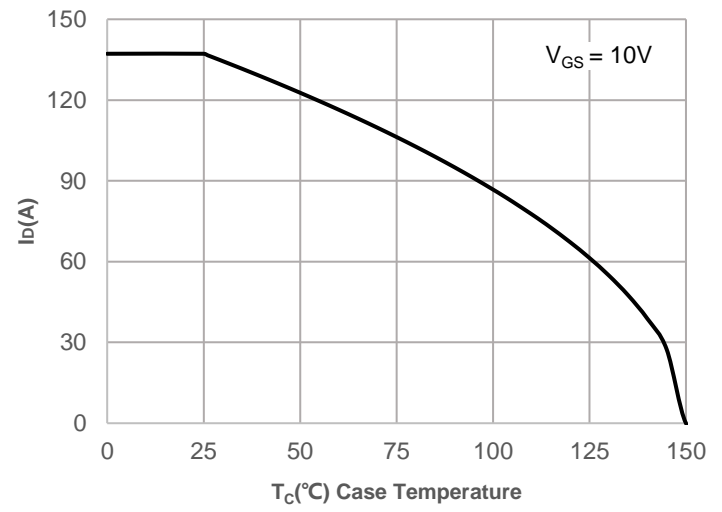
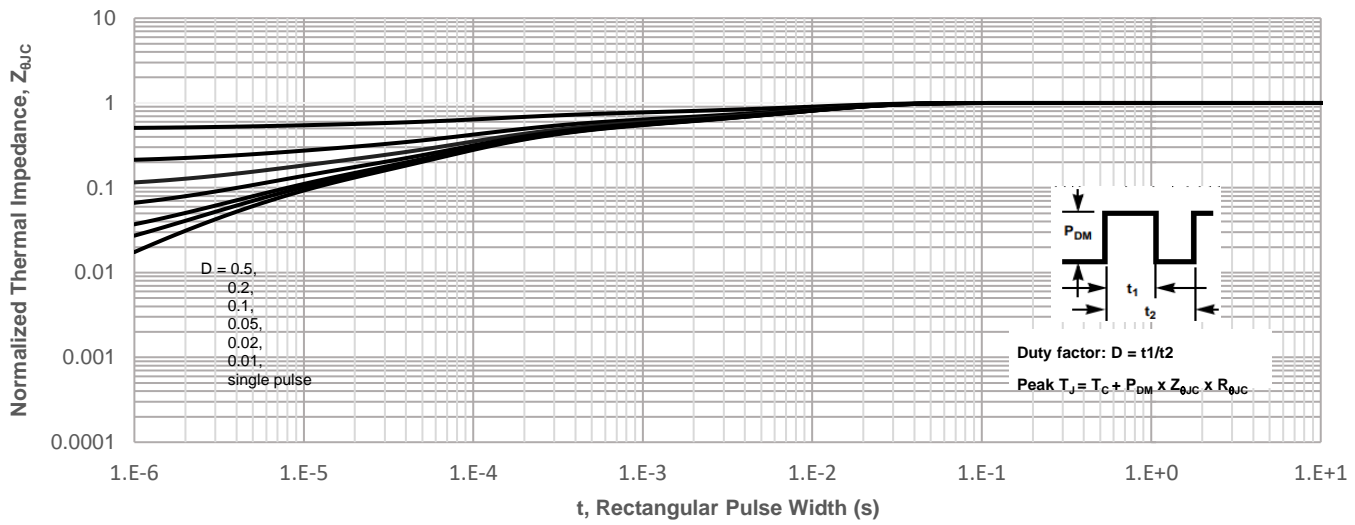
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	100	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 80\text{V}, V_{GS} = 0\text{V}$	-	-	1.0	$\mu\text{A}$
$I_{GSS}$	Gate-Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1.4	1.7	2.2	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance <sup>(4)</sup>	$V_{GS} = 10\text{V}, I_D = 20\text{A}$	-	3.3	4.3	m $\Omega$
		$V_{GS} = 4.5\text{V}, I_D = 20\text{A}$	-	4.5	5.8	m $\Omega$
<b>Dynamic Characteristics</b>						
$R_g$	Gate Resistance	$f = 1\text{MHz}$	-	1.6	-	$\Omega$
$C_{iss}$	Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = 50\text{V}, f = 1\text{MHz}$	3740	5236	7069	pF
$C_{oss}$	Output Capacitance		1086	1521	2053	pF
$C_{rss}$	Reverse Transfer Capacitance		13	18	25	pF
$Q_g$	Total Gate Charge	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 50\text{V}, I_D = 20\text{A}$	55	77	104	nC
$Q_{gs}$	Gate Source Charge		13	18	24	nC
$Q_{gd}$	Gate Drain("Miller") Charge		8	12	16	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-On DelayTime	$V_{GS} = 10\text{V}, V_{DD} = 50\text{V}$ $I_D = 20\text{A}, R_{GEN} = 3\Omega$	-	16	-	ns
$t_r$	Turn-On Rise Time		-	23	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	57	-	ns
$t_f$	Turn-Off Fall Time		-	16	-	ns
<b>Body Diode Characteristics</b>						
$I_S$	Maximum Continuous Body Diode Forward Current		-	-	137	A
$I_{SM}$	Maximum Pulsed Body Diode Forward Current		-	-	549	A
$V_{SD}$	Body Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = 20\text{A}$	-		1.2	V
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F = 20\text{A}, di/dt = 100\text{A}/\mu\text{s}$	74	103	139	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge		-	104	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
  2.  $E_{AS}$  condition: Starting  $T_J = 25^\circ\text{C}$ ,  $V_{DD} = 50\text{V}$ ,  $V_{GS} = 10\text{V}$ ,  $R_G = 25\Omega$ ,  $L = 3\text{mH}$ ,  $I_{AS} = 18.2\text{A}$ ,  $V_{DD} = 0\text{V}$  during time in avalanche.
  3.  $R_{\theta JA}$  is measured with the device mounted on a  $1\text{inch}^2$  pad of 2oz copper FR4 PCB.
  4. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 0.5\%$ .

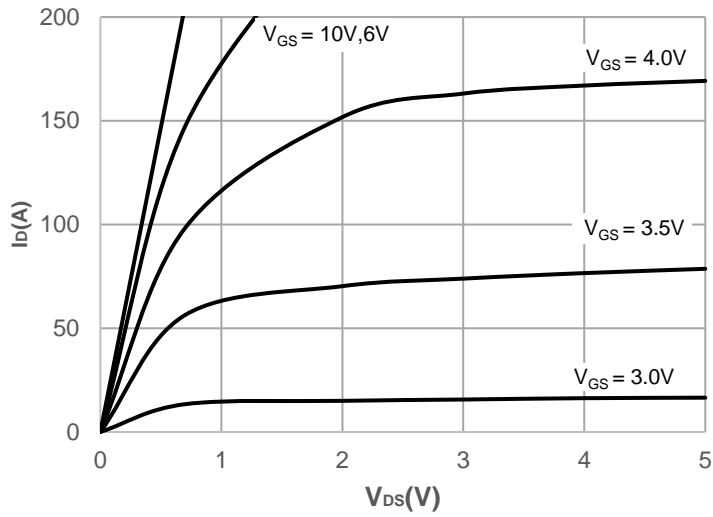
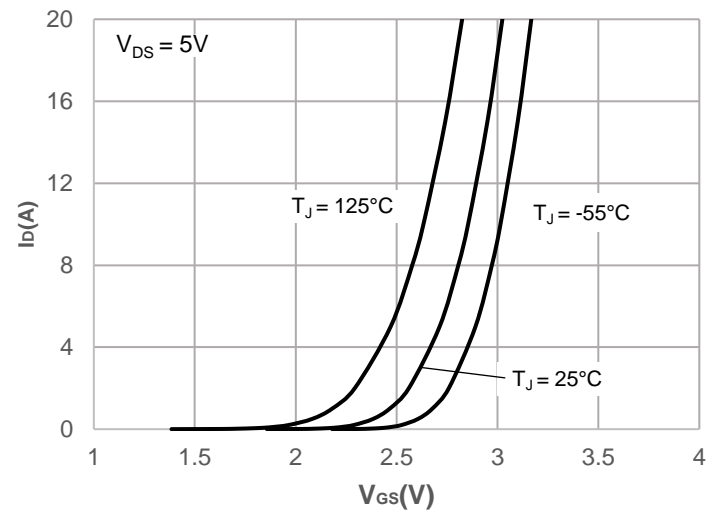
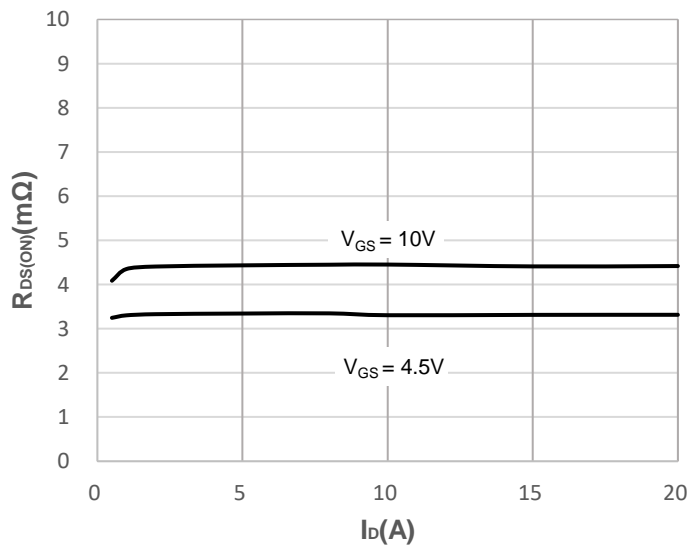
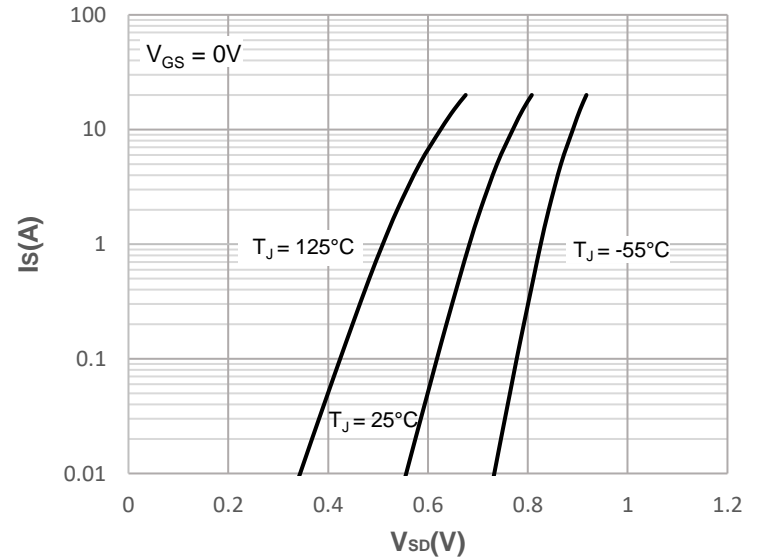
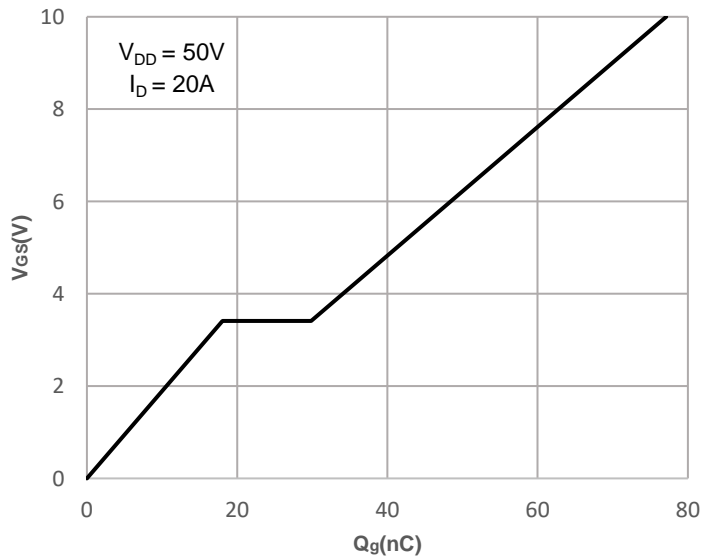
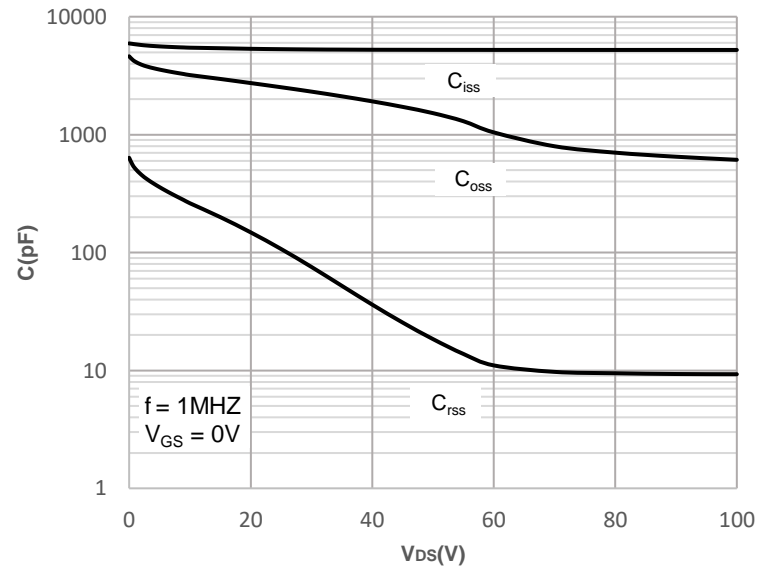


## Typical Performance Characteristics

**Figure 1: Power De-rating**

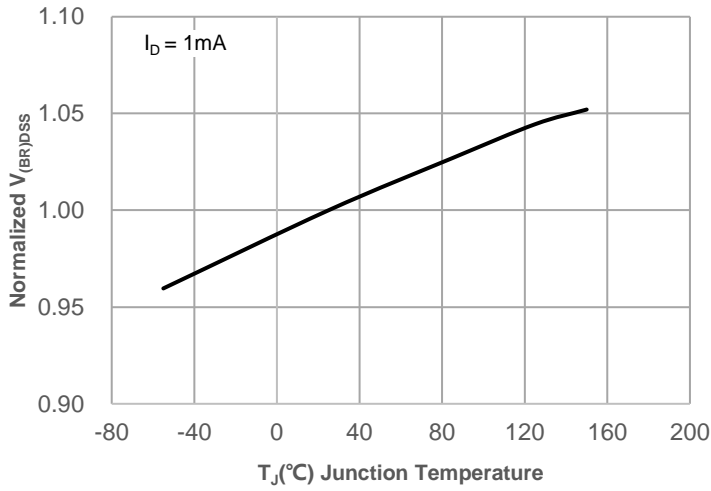
**Figure 2: Current De-rating**

**Figure 3: Normalized Maximum Transient Thermal Impedance**

**Figure 4: Peak Current Capacity**


## Typical Performance Characteristics

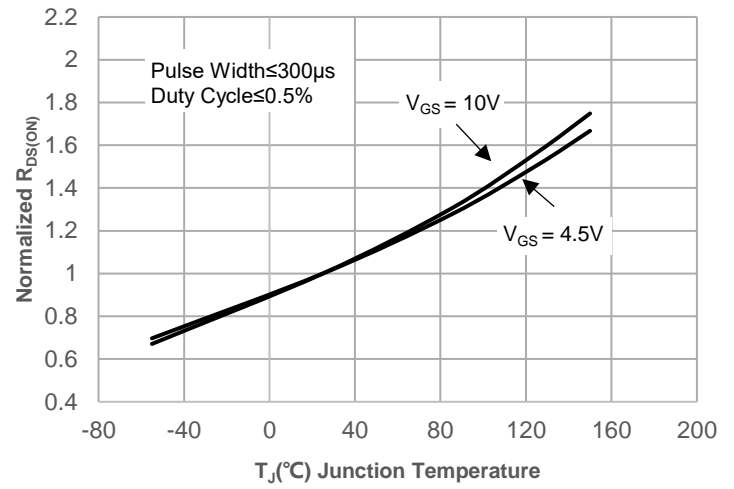
**Figure 5: Output Characteristics**

**Figure 6: Typical Transfer Characteristics**

**Figure 7: On-resistance vs. Drain Current**

**Figure 8: Body Diode Characteristics**

**Figure 9: Gate Charge Characteristics**

**Figure 10: Capacitance Characteristics**


## Typical Performance Characteristics

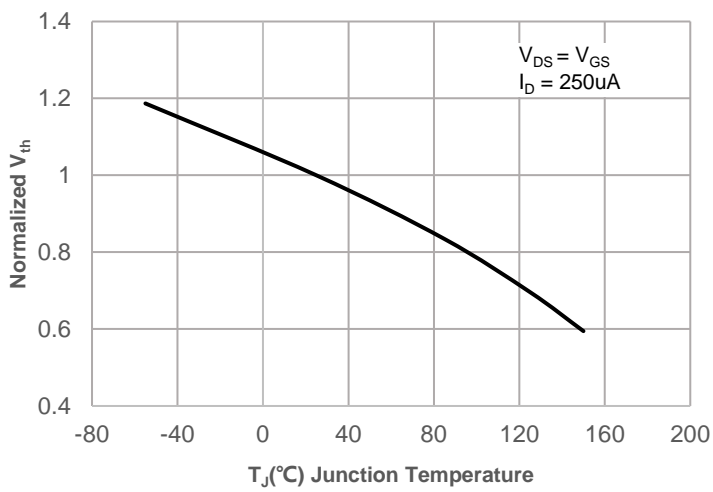
**Figure 11: Normalized Breakdown voltage vs. Junction Temperature**



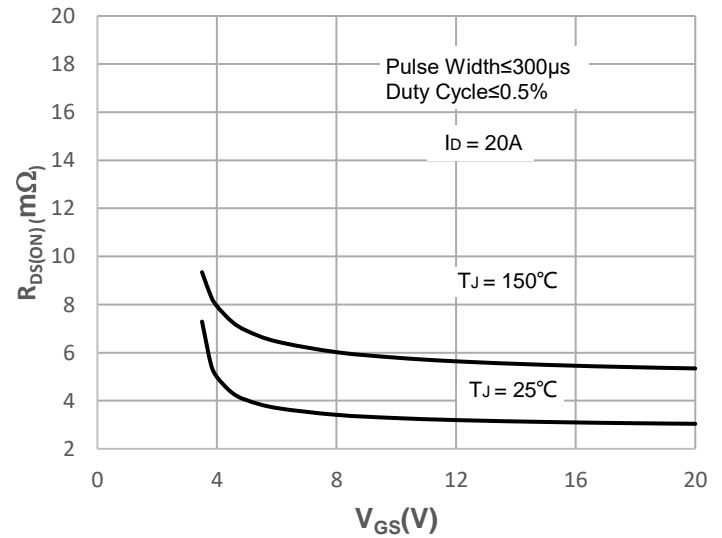
**Figure 12: Normalized on Resistance vs. Junction Temperature**



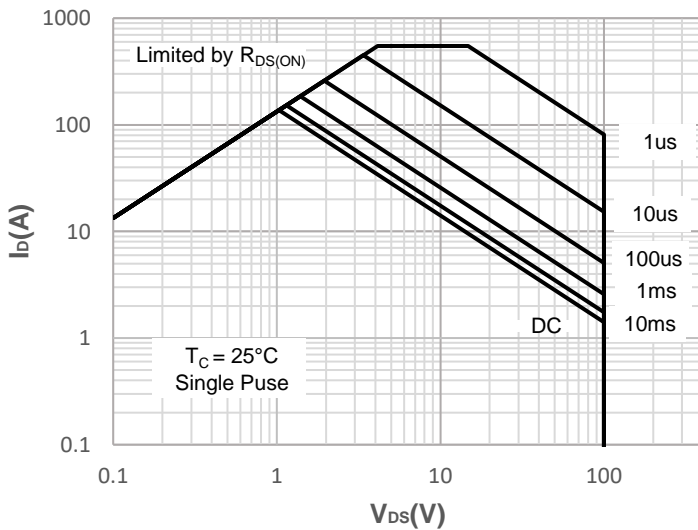
**Figure 13: Normalized Threshold Voltage vs. Junction Temperature**



**Figure 14: R\_DS(ON) vs. V\_GS**



**Figure 15: Maximum Safe Operating Area**



### Test Circuit



Figure 1: Gate Charge Test Circuit & Waveform

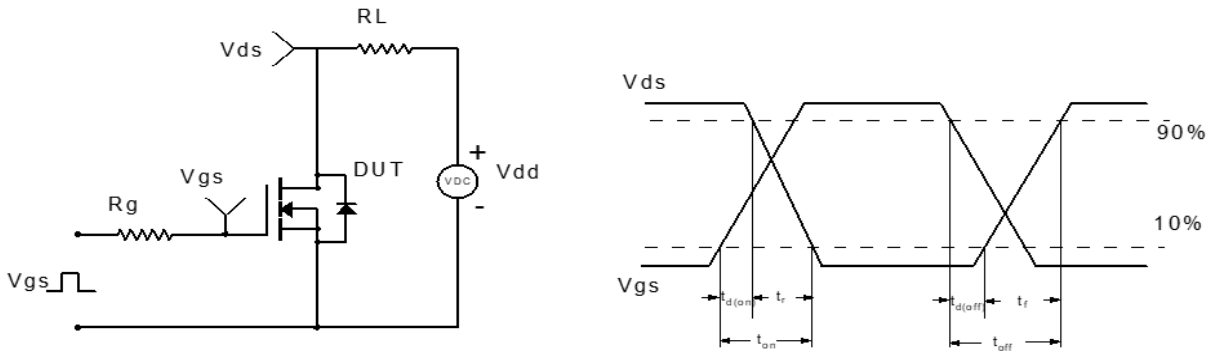


Figure 2: Resistive Switching Test Circuit & Waveform

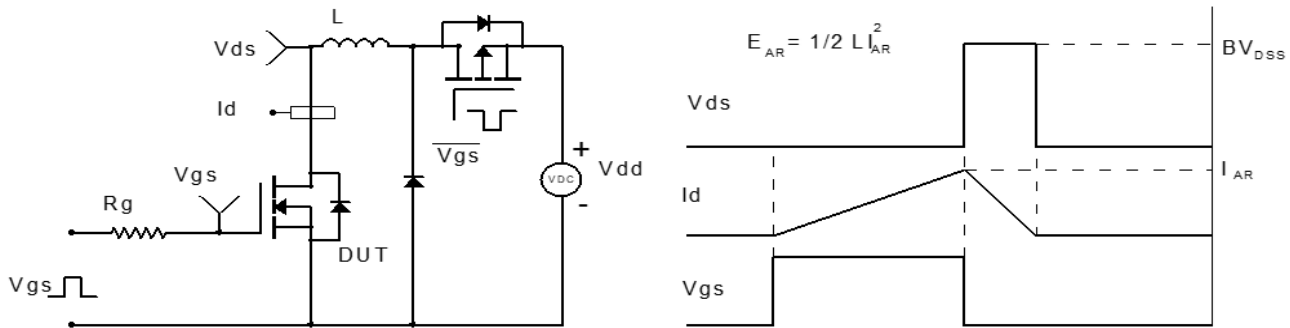


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

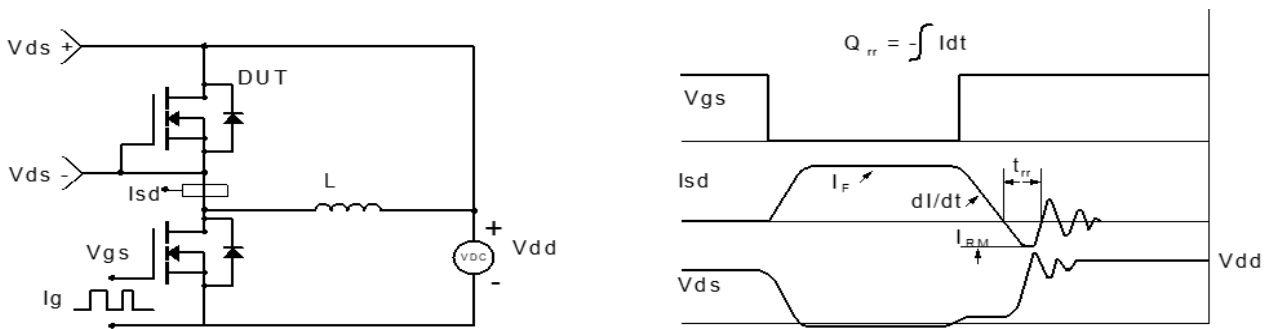
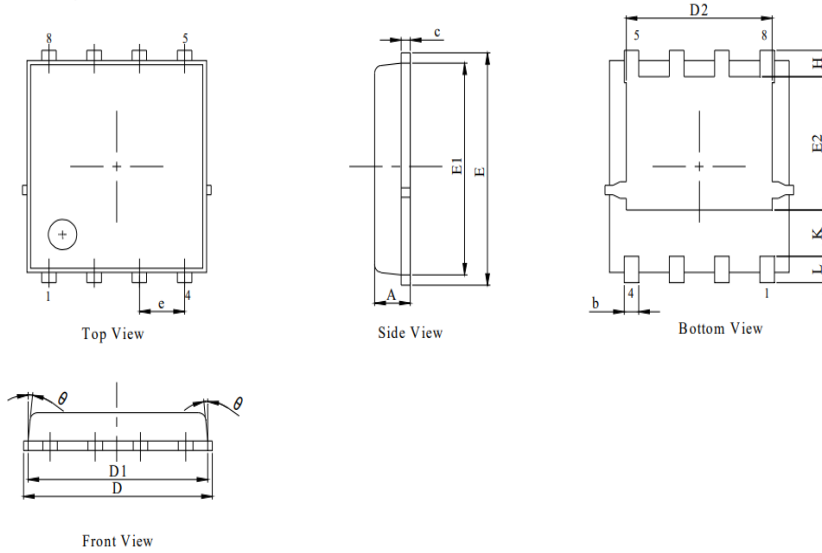


Figure 4: Diode Recovery Test Circuit & Waveform



## Package Mechanical Data(PDFN5X6-8L)

### Package Outline

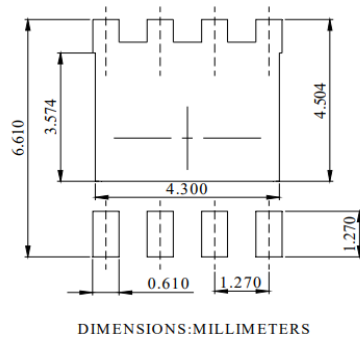


#### NOTES:

1. Dimension and tolerance per ASME Y14.5M, 1994.
2. All dimensions in millimeter (angle in degree).
3. Dimensions  $D1$  and  $E1$  do not include mold flash protrusions or gate burrs.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.9	1	1.15
b	0.31	0.41	0.51
C	0.24	0.32	0.4
D	5	5.2	5.4
D1	4.95	5.05	5.15
D2	4	4.1	4.2
E	6.05	6.15	6.25
E1	5.5	5.6	5.7
E2	3.42	3.53	3.63
e	1.27BSC		
H	0.6	0.7	0.8
L	0.5	0.7	0.8
K	1.23 REF		
0			10

### Recommended Soldering Footprint



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